Xintian

List of Publications by Year
in descending order

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21	360	9	15
papers	citations	h-index	g-index

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21	21	21	279
all docs	docs citations	times ranked	citing authors

#	ARTICLE	IF	CITATIONS
1	Investigations on the Degradation of 1.2-kV 4H-SiC MOSFETs Under Repetitive Short-Circuit Tests. IEEE Transactions on Electron Devices, 2016, 63, 4346-4351.	3.0	63
2	A Deep Insight Into the Degradation of 1.2-kV 4H-SiC mosfets Under Repetitive Unclamped Inductive Switching Stresses. IEEE Transactions on Power Electronics, 2018, 33, 5251-5261.	7.9	60
3	A Simulation-Based Comparison Between Si and SiC MOSFETs on Single-Event Burnout Susceptibility. IEEE Transactions on Electron Devices, 2019, 66, 2551-2556.	3.0	51
4	4H-SiC Trench MOSFET With Floating/Grounded Junction Barrier-controlled Gate Structure. IEEE Transactions on Electron Devices, 2017, 64, 4568-4574.	3.0	45
5	SiC Double-Trench MOSFETs With Embedded MOS-Channel Diode. IEEE Transactions on Electron Devices, 2020, 67, 582-587.	3.0	32
6	Single-Event Effects in SiC Double-Trench MOSFETs. IEEE Transactions on Nuclear Science, 2019, 66, 2312-2318.	2.0	26
7	SiC Planar MOSFETs With Built-In Reverse MOS-Channel Diode for Enhanced Performance. IEEE Journal of the Electron Devices Society, 2020, 8, 619-625.	2.1	24
8	Degradation of Radiation-Hardened Vertical Double-Diffused Metal-Oxide-Semiconductor Field-Effect Transistor During Gamma Ray Irradiation Performed After Heavy Ion Striking. IEEE Electron Device Letters, 2020, 41, 216-219.	3.9	15
9	Gate Oxide Damage of SiC MOSFETs Induced by Heavy-Ion Strike. IEEE Transactions on Electron Devices, 2021, 68, 4010-4015.	3.0	11
10	Gate Bias Dependence of <i>V</i> _{TH} Degradation in Planar and Trench SiC MOSFETs Under Repetitive Short Circuit Tests. IEEE Transactions on Electron Devices, 2022, 69, 2521-2527.	3.0	9
11	Physicsâ€based spice model on the dynamic characteristics of silicon carbide Schottky barrier diode. IET Power Electronics, 2016, 9, 2803-2807.	2.1	7
12	A Simulation Study on Single-Event Burnout in Power Normally-off AlGaN/GaN HEMT. , 2019, , .		4
13	A Novel Split-Gate-Trench MOSFET Integrated With Normal Gate and Built-In Channel Diode. IEEE Journal of the Electron Devices Society, 2021, 9, 839-845.	2.1	4
14	Degradation of 4H-SiC MOSFETs under different short circuit test conditions: A simulation study. , 2017, , .		3
15	SiC double-trench MOSFETs with source-recessed structure for enhanced ruggedness. Japanese Journal of Applied Physics, 2021, 60, 124005.	1.5	2
16	Degradation in super-junction MOSFET under successive exposure of heavy ion strike and gamma ray irradiation. Microelectronics Reliability, 2022, 132, 114529.	1.7	2
17	Degradation of 650ÂV SiC double-trench MOSFETs under repetitive overcurrent switching stress. Microelectronics Reliability, 2022, 133, 114545.	1.7	2
18	N-type lithium-nitrogen codoping in diamond from first principles. , 2017, , .		0

#	Article	IF	Citations
19	Short-circuit Failure Mechanism of SiC Double-trench MOSFET. , 2020, , .		0
20	Investigation of 1200 V 4H-SiC Junction Barrier Schottky Diode with Built-in MOSFET. , 2021, , .		0
21	Investigation of Anti-SEB Capability of 160 V Power MOSFET Device with Multiple Buffer Layer. , 2021, , .		0